Reflective Object Sensor

OPB606A, OPB606B, OPB606C OPB607A, OPB607B, OPB607C





Features:

- Choice of phototransistor (OPB606) or photodarlington (OPB607) output
- · Unfocused for sensing diffuse surface
- · Low cost plastic housing
- Filtered (OPB606, OPB607)

Description:

OPB606 consists of an infrared Light Emitting Diode (LED) and an NPN silicon phototransistor which are mounted "side-by-side" on parallel axes in a black opaque plastic housing.

The **OPB607** consists of an infrared Light Emitting Diode (LED) and an NPN silicon photodarlington which are mounted "side -by-side" on parallel axes in a black plastic housing.

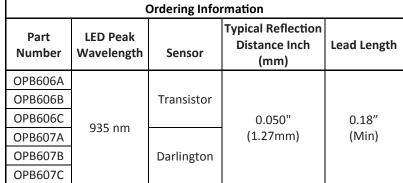
The emitting diode and phototransistor of both the **OPB606** and **OPB607** are encapsulated in a filtering epoxy that reduces ambient light noise. On both models, the phototransistors respond to radiation from the emitter only when a reflective object passes within the field of view.

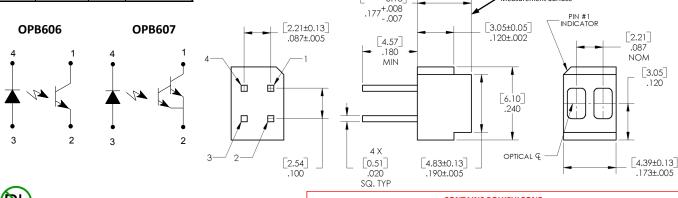
Custom electrical, wire and cabling and connectors are available. Contact your local representative or OPTEK for more information.

Applications:

- Non-contact reflective object sensor
- Assembly line automation
- Machine automation
- Machine safety
- End of travel sensor
- Door sensor

Pin#	LED	Pin#	Transistor	
4	Cathode	1	Collector	
3	Anode	2	Emitter	





4.50^{+0.20} -0.18

Pb

DIMENSIONS ARE IN: [MILLIMETERS] INCHES

CONTAINS POLYSULFONE

To avoid stress cracking, we suggest using ND Industries' **Vibra-Tite** for thread-locking. **Vibra-Tite** evaporates fast without causing structural failure in OPTEK's molded plastics.

Reflective Object Sensor

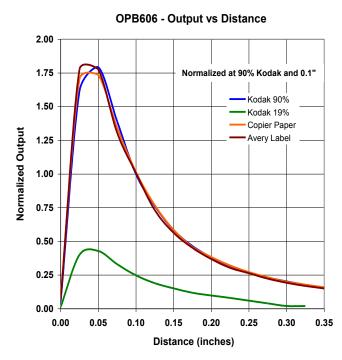
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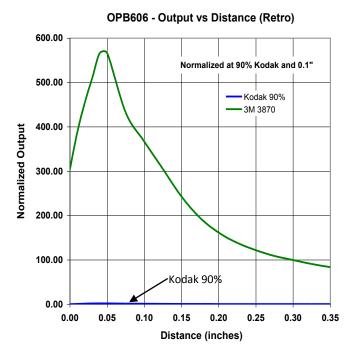


Absolute Maximum Ratings (T _A = 25° C unless otherwise noted)	
Storage & Operating Temperature Range	-40° C to +85° C
Lead Soldering Temperature [1/16 inch (1.6 mm) from the case for 5 sec. with soldering iron] (1)	260° C
Input Diode	
Forward DC Current	50 mA
Peak Forward Current (1 µs pulse width, 300 pps)	3 A
Reverse DC Voltage	2 V
Power Dissipation ⁽²⁾	75 mW
Output Phototransistor (OPB606) / Output Photodarlington (OPB607)	
Collector-Emitter Voltage	
OPB606A, OPB606B, OPB606C	30 V
OPB607A, OPB607B, OPB607C	15 V
Emitter-Collector Voltage	5 V
Collector DC Current	
OPB606A, OPB606B, OPB606C	25 mA
OPB607A, OPB607B, OPB607C	125 mA
Power Dissipation ⁽²⁾	75 mW

Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (2) Derate linearly 1.25 mW/°C above 25° C.





General Note TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

Reflective Object Sensor

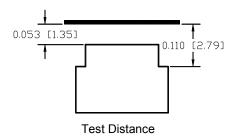
OPB606A, OPB606B, OPB606C OPB607A, OPB607B, OPB607C



Electrical Characteristics (T _A = 25° C unless otherwise noted)								
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS		
Input Diode (See OP165 for additional information)								
V _F	Forward Voltage	-	-	1.7	V	I _F = 20 mA		
I _R	Reverse Current	-	-	100	μΑ	V _R = 2 V		
Output Phototransistor (see OP268 for additional information—for reference only)								
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage OPB606 OPB607	30 15			V V	Ι _C = 100 μΑ		
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5	-	-	V	Ι _Ε = 100 μΑ		
I _{CEO}	Collector Dark Current OPB606 OPB607	-	-	100 250	nA nA	V _{CE} = 5 V, I _F = 0		
Combined (see OP508 or OP509 for additional information—for reference only)								
V _{CE(SAT)}	Collector-Emitter Saturation Voltage OPB606 OPB607	- -	- -	0.4 1.1	V	$I_F = 20 \text{ mA}, I_C = 100 \mu\text{A}, d = 0.053'' (1.45 \text{mm})^{(1)(2)}$ $I_F = 20 \text{mA}, I_C = 2 \text{mA}, d = 0.053'' (1.45 \text{mm})^{(1)(2)}$		
I _{C(ON)}	On-State Collector Current OPB606A OPB606B OPB606C OPB607A OPB607B OPB607C	500 350 200 25 17 10	- - - - -	- - - - -	μΑ μΑ μΑ mA mA	I _F = 20 mA, V _{ce} = 5 V, d = 0.053" (1.45 mm) ⁽¹⁾⁽²⁾		
I _{C(OFF)}	Off-State Collector Current OPB606 OPB607		- -	200 10	nΑ μΑ	V _{CE} = 5 V, I _F = 20 mA ⁽³⁾ V _{CE} = 5 V, I _F = 20 mA ⁽³⁾		

Notes:

- (1) "d" is the distance from the assembly measurement surface to the reflective surface.
- (2) Measured using Eastman Kodak neutral white test card with 90% diffuse reflectance as a reflecting surface. Reference: Eastman Kodak, Catalog # E 152 7795.
- (3) On OPB606, off-state collector current I_{C(OFF)} is measured with no reflective surface in the optical path. On OPB607, Crosstalk (I_{cx}) is the collector current measured with the indicated current in the input diode and with no reflecting surface.
- (4) All parameters tested using pulse techniques.



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